HSBA6048

N-Ch 60V Fast Switching MOSFETs

Description

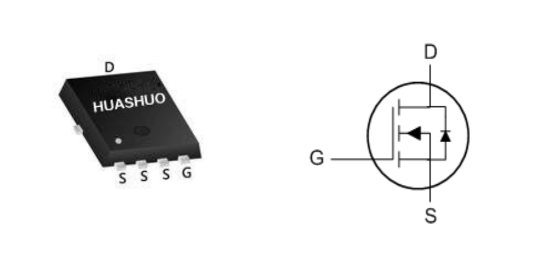
The HSBA6048 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.
The HSBA6048 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

V_{DS}	60	V
$R_{DS(ON),max}$	3.6	mΩ
I_D	85	A

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

PRPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current[1,6]	85	A
I_D@T_C=100˚C	Continuous Drain Current[1,6]	66	A
I_{DM}	Pulsed Drain Current[2]	240	A
EAS	Single Pulse Avalanche Energy[3]	101	mJ
I_{AS}	Avalanche Current	45	A
P_D@T_C=25˚C	Total Power Dissipation[4]	83	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	---	55	˚C/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	---	1.5	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	3.0	3.6	mΩ
		V_{GS}=4.5V , I_D=15A	---	4.4	5.4	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	65	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.7	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=30V , V_{GS}=10V , I_D=20A	---	58	---	nC
Q_{gs}	Gate-Source Charge		---	16	---	
Q_{gd}	Gate-Drain Charge		---	4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3Ω, I_D=20A	---	18	---	ns
T_r	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50	---	
T_f	Fall Time		---	10.5	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , f=1MHz	---	3458	---	pF
C_{oss}	Output Capacitance		---	1522	---	
C_{rss}	Reverse Transfer Capacitance		---	22	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	55	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=20A , dI/dt=100A/µs , T_J=25℃	---	24	---	nS
Q_{rr}	Reverse Recovery Charge		---	85	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=40A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
6.The maximum current rating is package limited.

Typical Characteristics

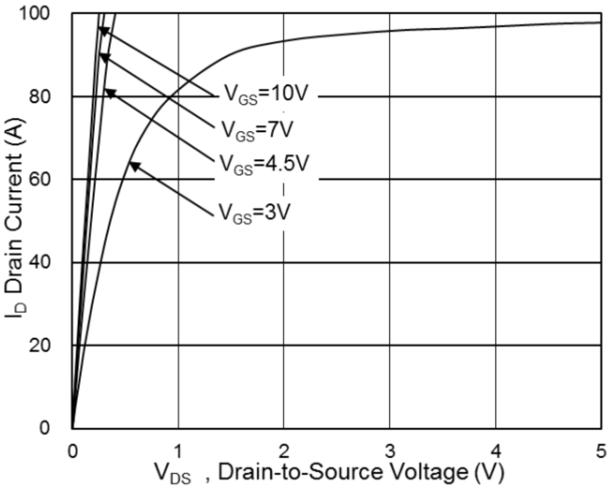


Fig.1 Typical Output Characteristics

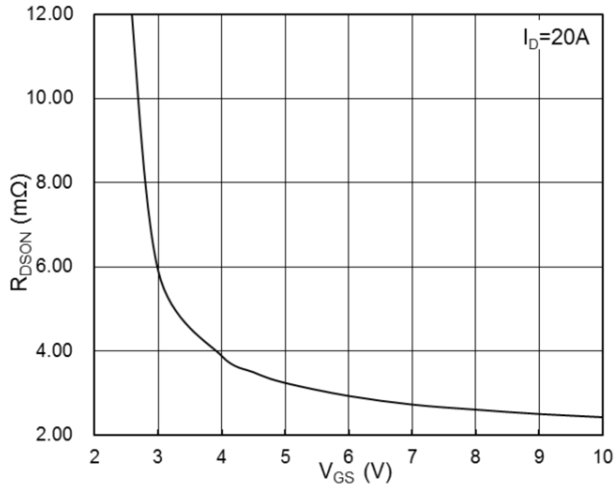


Fig.2 On-Resistance vs G-S Voltage

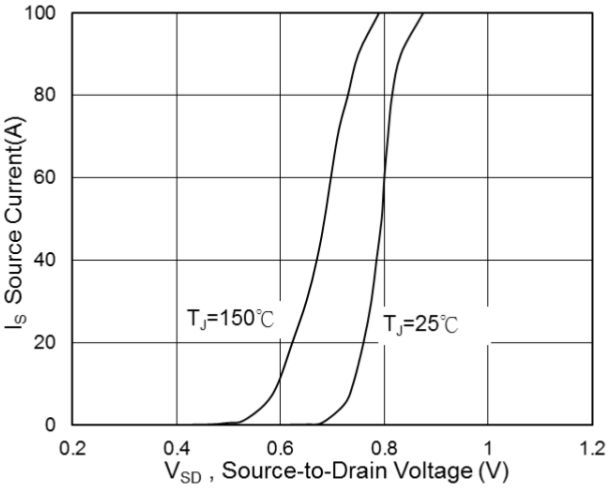


Fig.3 Diode Forward Voltage vs. Current

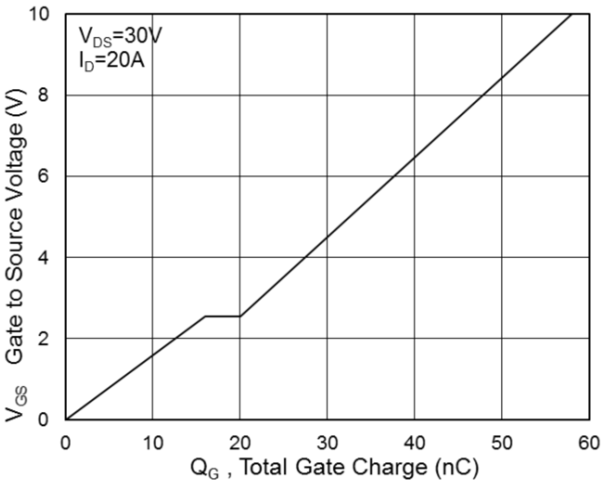


Fig.4 Gate-Charge Characteristics

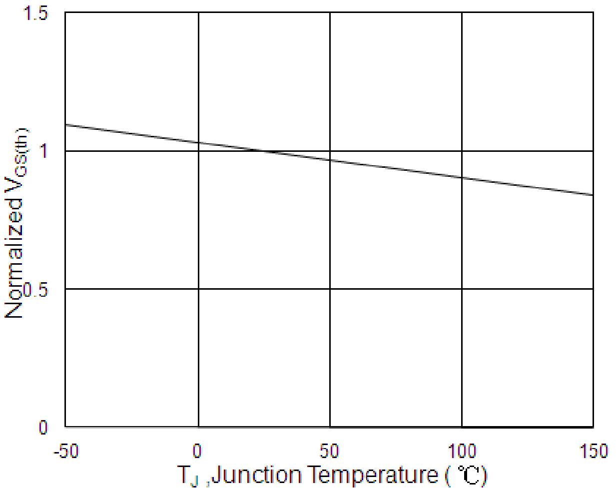


Fig.5 Normalized $V_{GS(th)}$ vs T_J

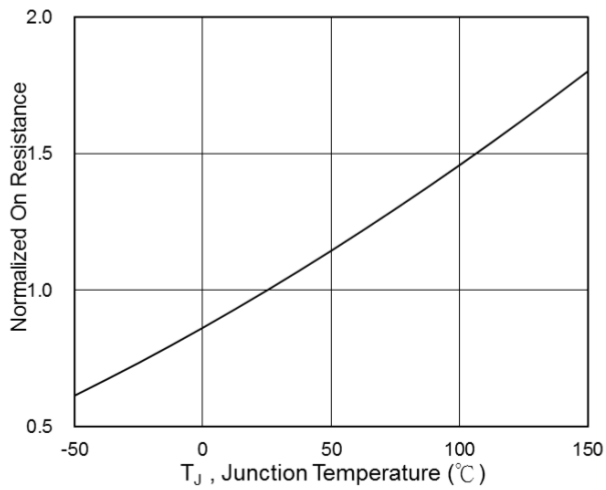


Fig.6 Normalized R_{DSON} vs T_J

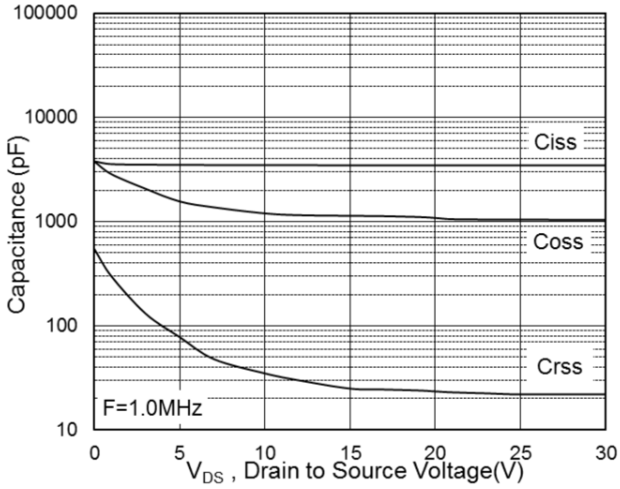


Fig.7 Capacitance

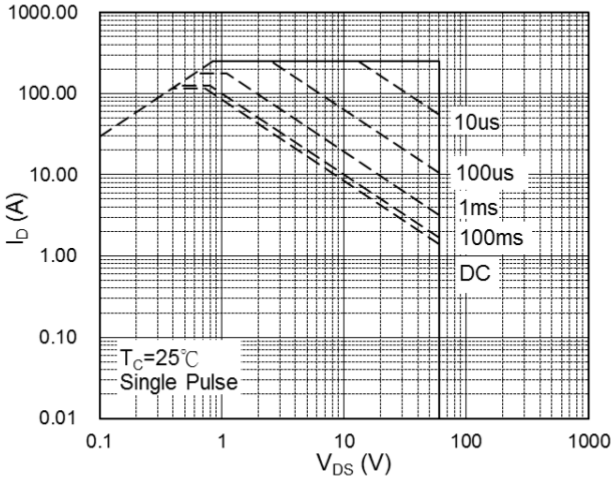


Fig.8 Safe Operating Area

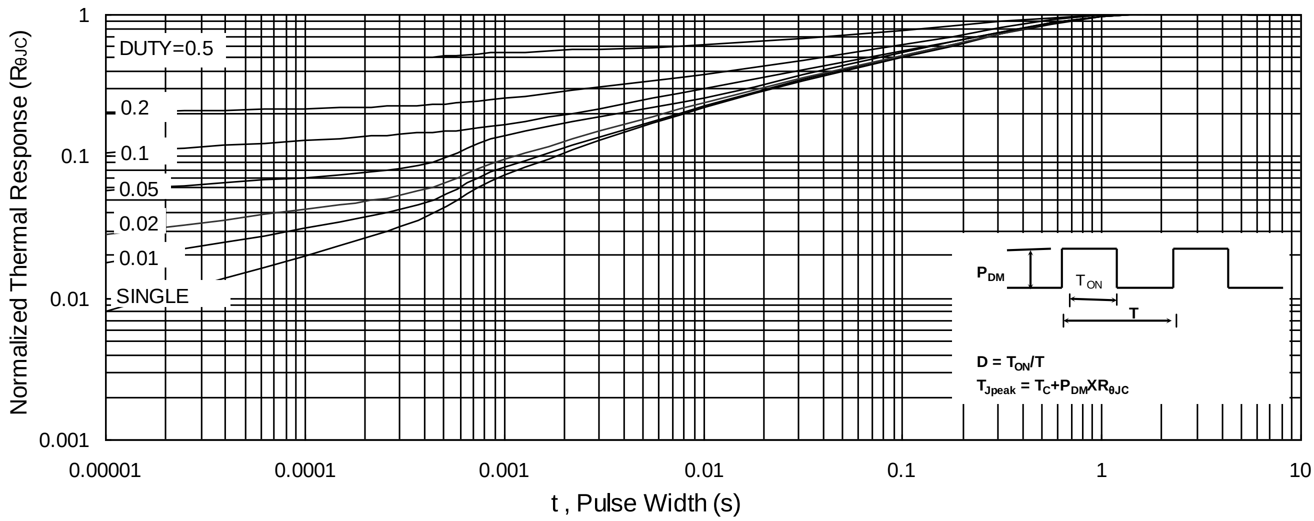


Fig.9 Normalized Maximum Transient Thermal Impedance

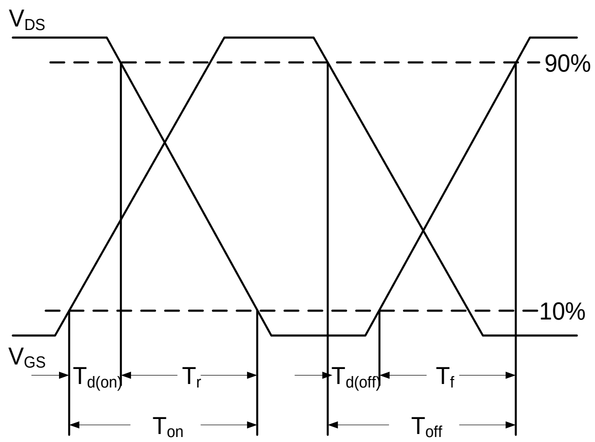


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

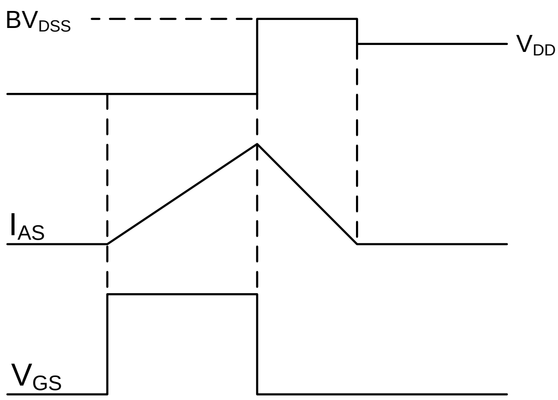


Fig.11 Unclamped Inductive Switching